



to and operatively connected with said [image] light sensor region
wherein said semiconductor layer has at least one of an electron mobility [15-
100] 15-300 cm²/V sec and a hole mobility [10-100] 10-200 cm²/V sec.

F2 SUB I10
13. (Amended) The device of claim 9 wherein said semiconductor layer has at
least one of an electron mobility in a range from [15 to 100] 15-300 cm²/V sec and a hole
mobility in a range from [10 to 100] 10-200 cm²/V sec.

14. (Amended) The device of claim 1 wherein said semiconductor layer has at
least one of an electron mobility in a range from [15 to 100] 15-300 cm²/V sec and a hole
mobility in a range from [10 to 100] 10-200 cm²/V sec.

F3 sub. I13
22. (Amended) A device for reading an image comprising:
a semiconductor layer formed on a substrate, said semiconductor layer
comprising an image sensor region and a semiconductor switch region adjacent to and
operatively connected with said image sensor region,
wherein said semiconductor layer has at least one of an electron mobility 15-
300 cm²/V sec and a hole mobility 10-200 cm²/V sec.

F4 SUB I20
27. (Amended) The device of claim 23 wherein said semiconductor layer has at
least one of an electron mobility in a range from 15 to 300 cm²/V sec and a hole mobility
in a range from 10 to 200 cm²/V sec.

28. (Amended) The device of claim 15 wherein said semiconductor layer has at
least one of an electron mobility in a range from 15 to 300 cm²/V sec and a hole mobility
in a range from 10 to 200 cm²/V sec.

Please add the following new claims:



31. A semiconductor device comprising:

a substrate;

a blocking layer on said substrate;

first and second semiconductor islands on said blocking layer;

a pair of p-type impurity regions in said first semiconductor island with a first channel region interposed therebetween;

a pair of n-type impurity regions in said second semiconductor island with a second channel region;

a gate insulating film on said first and second semiconductor islands; and first and second gate electrodes over said first and second channel regions, respectively, with said gate insulating film interposed therebetween,

wherein a Raman spectrum of each of said first and second semiconductor islands exhibits a peak deviated from that which stands for a single crystal of the semiconductor.

32. A device according to claim 31, wherein said blocking layer comprises silicon oxide

33. A device according to claim 31, wherein said gate insulating film is a silicon oxide film containing fluorine.

34. A device according to claim 31, said p-type impurity regions contain boron.

35. A device according to claim 31, said N-type impurity regions contain phosphorus.



36. A semiconductor device comprising:
a substrate;
a blocking layer on said substrate;
first and second semiconductor islands on said blocking layer;
a pair of p-type impurity regions in said first semiconductor island with a first
channel region interposed therebetween;
a pair of n-type impurity regions in said second semiconductor island with
a second channel region;
a gate insulating film on said first and second semiconductor islands; and
first and second gate electrodes over said first and second channel regions,
respectively, with said gate insulating film interposed therebetween,
wherein said first semiconductor island has a mobility of 10-300 cm²/Vsec
and said second semiconductor island has a mobility of 15-300 cm²/Vsec.

37. A device according to claim 32, wherein said blocking layer comprises silicon
oxide.

38. A device according to claim 32, wherein said gate insulating film is a silicon
oxide film containing fluorine.

39. A device according to claim 32, said p-type impurity regions contain boron.

40. A device according to claim 32, said N-type impurity regions contain
phosphorus.

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